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Data Sheet

September 2013

N-Channel Logic Level Power MOSFET 50V, 16A, 47 $m\Omega$

These are N-Channel logic level power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use with logic level (5V) driving sources in applications such as programmable controllers, switching regulators, switching converters, motor relay drivers and emitter switches for bipolar transistors. This performance is accomplished through a special gate oxide design which provides full rated conductance at gate biases in the 3V to 5V range, thereby facilitating true on-off power control directly from logic circuit supply voltages.

Formerly developmental type TA09871.

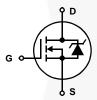
Ordering Information

	PART NUMBER	PACKAGE	BRAND
RI	FD16N05LSM9A	TO-252AA	RFD16N05LSM

Features

- 16A, 50V
- $r_{DS(ON)} = 0.047\Omega$
- UIS SOA Rating Curve (Single Pulse)
- · Design Optimized for 5V Gate Drives
- · Can be Driven Directly from CMOS, NMOS, TTL Circuits
- SOA is Power Dissipation Limited
- · Nanosecond Switching Speeds
- Linear Transfer Characteristics
- · High Input Impedance
- · Majority Carrier Device
- · Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging

JEDEC TO-252AA



RFD16N05LSM

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	RFD16N05LSM9A	UNITS
Drain to Source Voltage (Note 1)V _{DS}	50	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	50	V
Continuous Drain Current	16	Α
Pulsed Drain Current (Note 3)	45	Α
Gate to Source Voltage	±10	V
Maximum Power Dissipation	60	W
Derate Above 25°C	0.48	W/oC
Operating and Storage Temperature	-55 to 150	°С
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	οС
Package Body for 10s, See Techbrief 334	260	oC

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE

1. $T_J = 25^{\circ}C$ to $125^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250mA, V _{GS} = 0V, Figure 10		50	-	-	V
Gate to Threshold Voltage	e to Threshold Voltage $V_{GS(TH)}$ $V_{GS} = V_{DS}$, $I_D = 250$ mA, Figure 9		1	-	2	V	
Zero Gate Voltage Drain Current	I _{DSS}	I_{DSS} $V_{DS} = 40V, V_{GS} = 0V$		-	-	1	μΑ
			$T_{\rm C} = 150^{\rm o}{\rm C}$	-	-	50	μΑ
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 10V, V_{DS} =$	= 0V	-	-	100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	I _D = 16A, V _{GS} = 5V		-	-	0.047	Ω
		I _D = 16A, V _{GS} = 4V		-	-	0.056	Ω
Turn-On Time	t _(ON)	$V_{DD} = 25V$, $I_{D} = 8A$, $V_{GS} = 5V$, $R_{GS} = 12.5\Omega$ Figures 15, 16		-	-	60	ns
Turn-On Delay Time	t _{d(ON)}			-	14	-	ns
Rise Time	t _r			-	30	-	ns
Turn-Off Delay Time	t _{d(OFF)}			-	42	-	ns
Fall Time	t _f			-	14	-	ns
Turn-Off Time	t _(OFF)			-	-	100	ns
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 10V	V _{DD} = 40V,	-	-	80	nC
Gate Charge at 5V	Q _{g(5)}	$V_{GS} = 0V \text{ to } 5V$ $I_{D} = 16A,$ $R_{L} = 2.5\Omega$ Figures 17, 18	-	-	45	nC	
Threshold Gate Charge	Q _{g(TH)}		_	-	-	3	nC
Thermal Resistance Junction to Case	$R_{ heta JC}$		1	-17	-	2.083	°C/W
Thermal Resistance Junction to Ambient R_{θ}				-	-	100	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V _{SD}	I _{SD} = 16A	-	-	1.5	V
Diode Reverse Recovery Time	t _{rr}	$I_{SD} = 16A$, $dI_{SD}/dt = 100A/\mu s$	1	1	125	ns

NOTES:

- 2. Pulse Test: Pulse Width ≤300ms, Duty Cycle ≤2%.
- 3. Repetitive Rating: Pulse Width limited by max junction temperature.

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Typical Performance Curves Unless Otherwise Specified

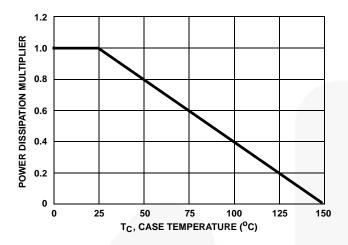


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

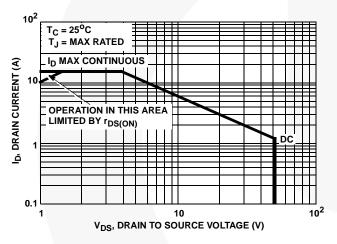


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

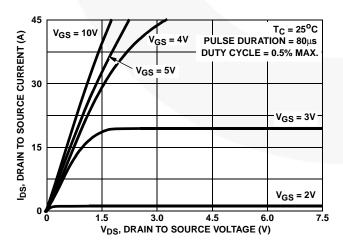


FIGURE 5. SATURATION CHARACTERISTICS

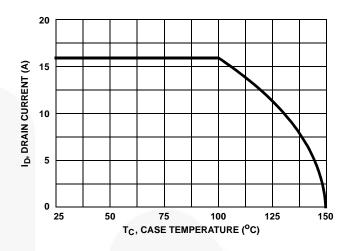


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

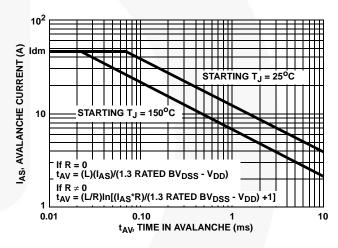


FIGURE 4. UNCLAMPED INDUCTIVE SWITCHING SOA (SINGLE PULSE UIS SOA)

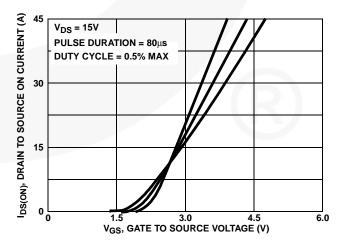


FIGURE 6. TRANSFER CHARACTERISTICS

Typical Performance Curves Unless Otherwise Specified (Continued)

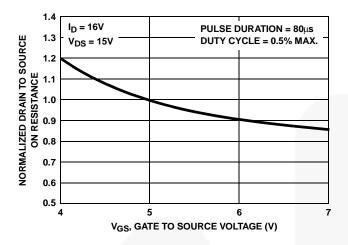


FIGURE 7. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

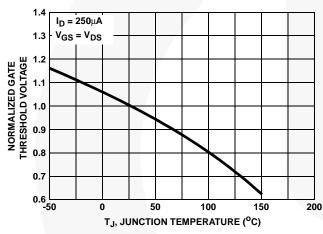


FIGURE 9. NORMALIZED GATE THRESHOLD VS JUNCTION TEMPERATURE

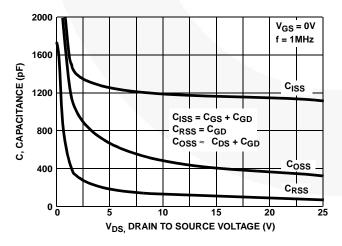


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

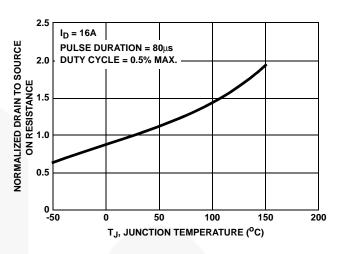


FIGURE 8. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

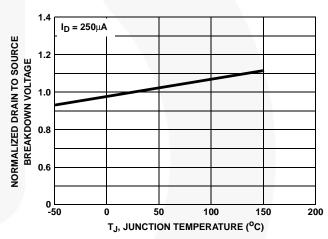


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

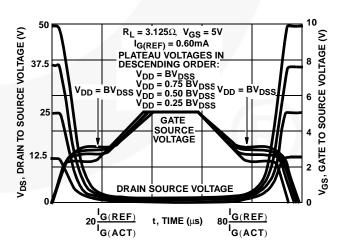


FIGURE 12. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

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Test Circuits and Waveforms

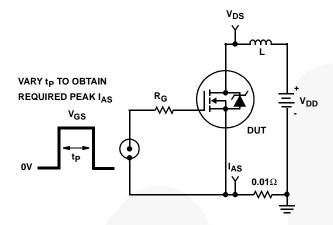


FIGURE 13. UNCLAMPED ENERGY TEST CIRCUIT

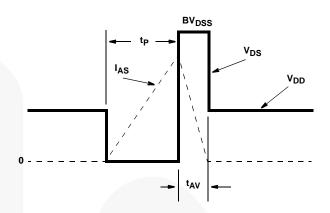


FIGURE 14. UNCLAMPED ENERGY WAVEFORMS

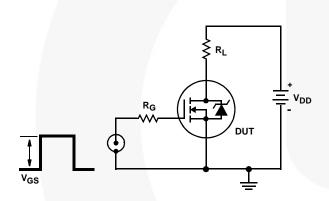


FIGURE 15. SWITCHING TIME TEST CIRCUIT

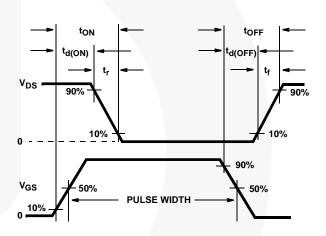


FIGURE 16. RESISTIVE SWITCHING WAVEFORMS

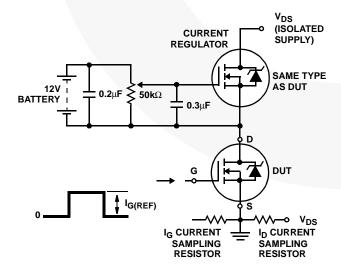


FIGURE 17. GATE CHARGE TEST CIRCUIT

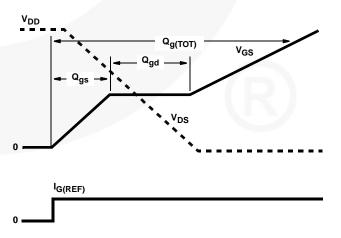


FIGURE 18. GATE CHARGE WAVEFORMS

PSPICE Electrical Model

.SUBCKT RFD16N05L 2 1 3; REV 4/8/92

Ca 12 8 3.33e-9 Cb 15 14 3.11e-9 Cin 6 8 1.21e-9

Dbody 7 5 DBDMOD Dbreak 5 11 DBKMOD Dplcap 10 5 DPLCAPMOD

Ebreak 11 7 17 18 70.9 Eds 14 8 5 8 1 Egs 13 8 6 8 1 Esg 6 10 6 8 1 Evto 20 6 18 8 1

IT 8 17 1

Lgate 1 9 1.38e-9 Ldrain 2 5 1.0e-12 Lsource 3 7 1.0e-9

Mos1 16 6 8 8 MOSMOD M=0.99 Mos2 16 21 8 8 MOSMOD M=0.01

Rin 6 8 1e9 Rbreak 17 18 RBKMOD 1 Rdrain 5 16 RDSMOD 27.38e-3 Rgate 9 20 2.98 Rsource 8 7 RDSMOD 0.614e-3 Rvto 18 19 RVTOMOD 1

S1a 6 12 13 8 S1AMOD S1b 13 12 13 8 S1BMOD S2a 6 15 14 13 S2AMOD S2b 13 15 14 13 S2BMOD

Vbat 8 19 DC 1 Vto 21 6 0.448

.MODEL DBDMOD D (IS=1.34e-13 RS=1.21e-2 TRS1=1.64e-3 TRS2=2.59e-6

+CJO=1.13e-9 TT=4.14e-8)

.MODEL DBKMOD D (RS=8.82e-2 TRS1=-2.01e-3 TRS2=7.32e-10)

.MODEL DPLCAPMOD D (CJO=0.522e-9 IS=1e-30 N=10)

.MODEL MOSMOD NMOS (VTO=2.054 KP=24.73 IS=1e-30 N=10 TOX=1 L=1u W=1u)

.MODEL RBKMOD RES (TC1=1.01e-3 TC2=5.21e-8)

.MODEL RDSMOD RES (TC1=3.66e-3 TC2=1.46e-5)

.MODEL RVTOMOD RES (TC1=-1.81e-3 TC2=1.41e-6)

.MODEL S1AMOD VSWITCH(RON=1e-5 ROFF=0.1 VON=-4.25 VOFF=-2.25)

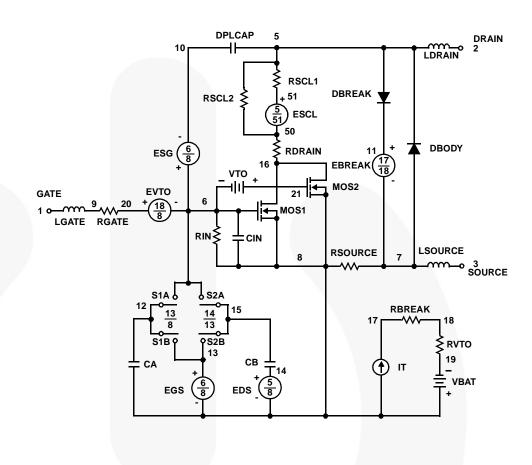
.MODEL S1BMOD VSWITCH(RON=1e-5 ROFF=0.1 VON=-2.25 VOFF=-4.25)

.MODEL S2AMOD VSWITCH(RON=1e-5 ROFF=0.1 VON=-0.65 VOFF=4.35)

.MODEL S2BMOD VSWITCH(RON=1e-5 ROFF=0.1 VON=4.35 VOFF=-0.65)

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; written by William J. Hepp and C. Frank Wheatley.





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